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**INFORMATION  
DISCLOSURE STATEMENT  
TRANSMITTAL**

To Commissioner For Patents

Enclosed herewith is a Form PTO-1449, any required copies of documents listed thereon, and any concise explanation of their relevance is indicated below per 37 CFR 1.97.

<i>Initials</i>	<i>Application Number</i>	<b>101563483</b>
	<i>Filing Date</i>	
	<i>First Named Inventor</i>	PONOMAREV YOURI
	<i>Group Art Unit</i>	2823
	<i>Examiner Name</i>	<i>M. Estrada</i>
	<i>Atty. Docket Number</i>	NL03 0833 US1

**U.S. PATENT DOCUMENTS**

<i>Examiner Initials</i>	<i>Cite No.<sup>1</sup></i>	<i>Document Number No.-Kind Code<sup>2</sup> (if known)</i>	<i>Publication Date MM-DD-YYYY</i>	<i>Name of Patentee or Applicant of Cited Document</i>	<i>Pages, Columns Lines, Where Relevant Passages or Relevant Figures Appear</i>
<i>ME</i>	1	US- 4 665 412	05/12/1987	OHKAWA TIHIRO	
<i>ME</i>	2	US- 4 695 857	09/22/1987	BABA TOSHIO	
<i>ME</i>	3	US- 5 055 887	10/08/1991	YAMAZAKI SHUNPEI	
<i>ME</i>	4	US- 4 908 678	03/13/1990	YAMAZAKI SHUNPEI	
		US-			
		US-			

**FOREIGN PATENT DOCUMENTS**

<i>Examiner Initials*</i>	<i>Cite No.<sup>1</sup></i>	<i>Document Number (dry<sup>3</sup>-no.-kind<sup>4</sup>, if known)</i>	<i>Publication Date MM-DD-YYYY</i>	<i>Name of Patentee or Applicant of cited document</i>	<i>Pages, Columns Lines, Where Relevant Passages or Relevant Figures Appear</i>	<i>T<sup>5</sup></i>

**NON-PATENT LITERATURE DOCUMENTS**

<i>Examiner Initials*</i>	<i>Cite No.<sup>1</sup></i>	<i>Include name of the author (in capital letters), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.</i>	<i>T<sup>5</sup></i>
<i>ME</i>	1	KOJI Y ET AL: "THE FORMATION OF RESONANCE TUNNEL DEVICE BY GAMMA-AL203/SI . . ."; EXTENDED ABSTRACTS OF THE INTERNATIONAL CONFERENCE ON SOLID STATE DEVICES AND MATERIALS; JAPAN SOCIETY OF APPLIED PHYSICS; TOKYO JA; Vol. 2001; 26-September 2001; pages 588-589	
	2	LU Z H ET AL: "CRYSTALLINE Si/SiO <sub>2</sub> QUANTUM WELLS"; APPLIED PHYSICS LETTERS, AMERICAN INSTITUTE OF PHYSICS; NEW YORK, US; Vol. 80, No. 2; 14 January 2002; pages 255-257	
<i>ME</i>	3	MEREU B ET AL: "FOWLER-NORDHEIM TUNNELING IN EPITAXIAL YTTRIUM OXIDE ON SILICON FOR HIGH-K GATE APPLICATIONS"; 2002 INTERNATIONAL SEMICONDUCTOR CONFERENCE; CAS 2002 PROCEEDINGS; IEEE PISCATAWAY; NJ USA; Vol. 2 8 Oct. 2002; pages 309-312	
<i>ME</i>	4	J. ALIEU ET AL: "MULTIPLE SiGe QUANTUM WELLS - NOVEL CHANNEL ARCHITECTURE FOR 0.2 CMOS"; PROCEEDINGS OF THE 29 <sup>TH</sup> EUROPEAN SOLID-STATE DEVICE RESEARCH CONFERENCE; LEUVEN, BELGIUM; 13-15 SEP. 1999; P. 292-295	

<i>Examiner Signature</i>	<i>M. Estrada</i>	<i>Date Considered</i>	<i>2/2/08</i>
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